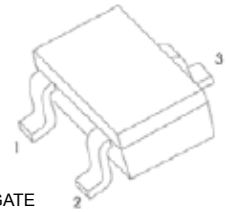
GOOD-ARK SEMICONDUCTOR

SSF3134K

20V N-Channel MOSFET

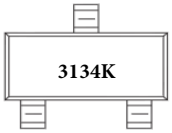
Main Product Characteristics

$V_{(BR)DSS}$	20V
$R_{DS(on)}$MAX	380 mΩ@4.5V
	450 mΩ@2.5V
	800 mΩ@1.8V
I_D	0.75A

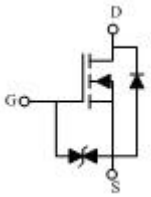


1. GATE
2. SOURCE
3. DRAIN

SOT-523



Marking and Pin Assignment



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for DC-DC converter, power management in portable battery, computer, printer, cellular and general purpose applications
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

RoHS Compliant

Description

The SSF3134K utilizes the latest processing techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in DC-DC converter, power management in portable battery, computer, printer, cellular and general purpose applications.

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source voltage	V_{DSS}	20	V
Typical Gate-Source Voltage	V_{GS}	±12	
Drain Current-Continuous	I_D	0.75	A
Drain Current -Pulsed (note1)	I_{DM}	3	
Power Dissipation (note 2)	P_D	150	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	℃/W
Storage Temperature	T_j	150	℃
Junction Temperature	T_{stg}	-55 to +150	

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Electrical Characteristics (T_A=25°C unless otherwise specified)

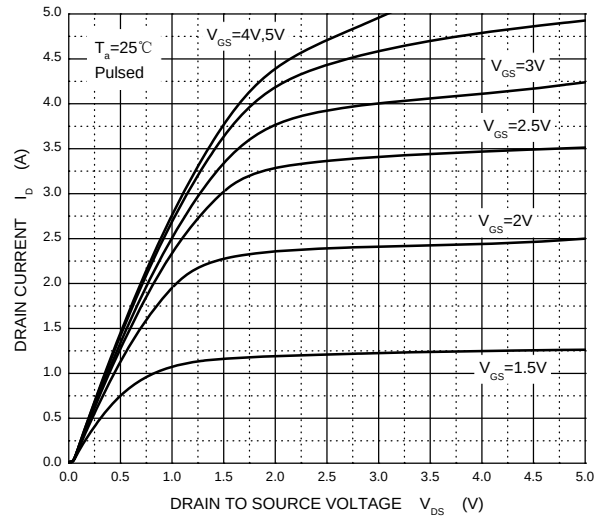
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
On/Off States						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Gate-Threshold Voltage (note 3)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.35		1.1	
Gate-Body Leakage Current	I_{GSS}	V_{DS} =0V, V_{GS} =±10V			±20	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =20V, V_{GS} =0V			1	μA
Drain-Source On-State Resistance(note 3)	$R_{DS(on)}$	V_{GS} =4.5V, I_D =650mA			380	mΩ
		V_{GS} =2.5V, I_D =550mA			450	
		V_{GS} =1.8V, I_D =450mA			800	
Forward Transconductance	g_{FS}	V_{DS} =10V, I_D =800mA	1			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} =16V,V_{GS} =0V,f =1MHz			120	pF
Output Capacitance	C_{oss}				20	
Reverse Transfer Capacitance	C_{rss}				15	
Switching Times						
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=10V,I_D=500mA, V_{GS}=4.5V,R_G=10Ω		6.7		ns
Rise Time	t_r			4.8		
Turn-Off Delay Time	$t_{d(off)}$			17.3		
Fall Time	t_f			7.4		
Drain-Source Diode Characteristics						
Drain-Source Diode Forward Voltage (note 3)	V_{SD}	I_S=0.15A, V_{GS} = 0V			1.2	V

Notes:

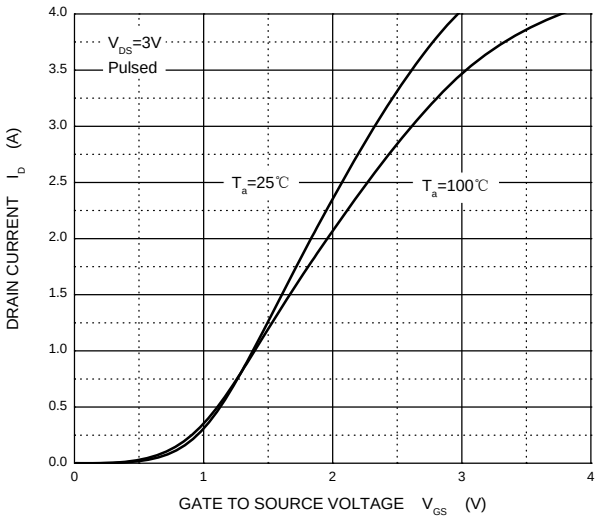
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at T_a=25℃.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Electrical and Thermal Characteristics

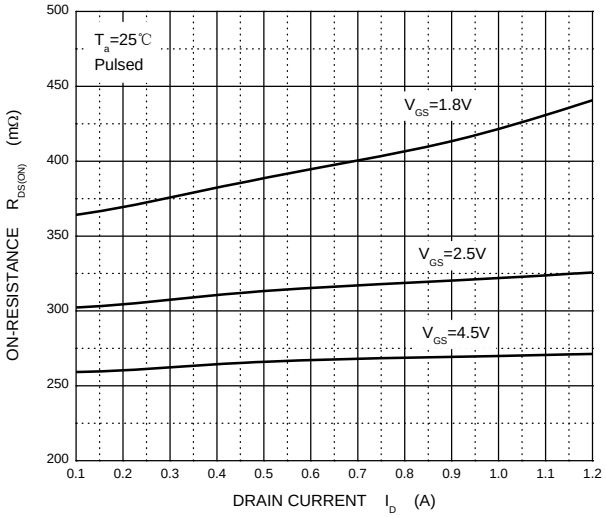
Output Characteristics



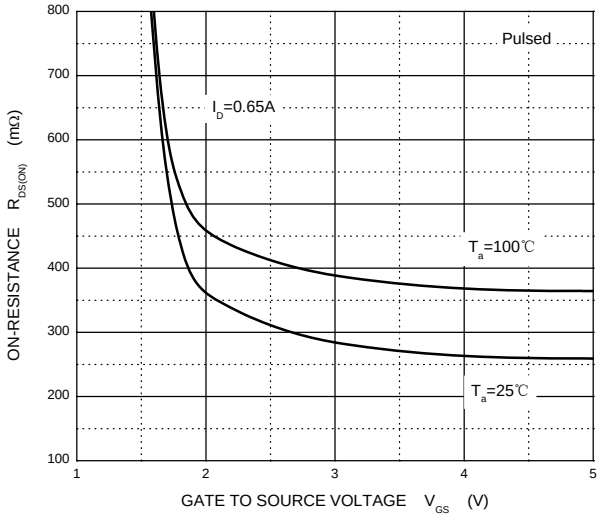
Transfer Characteristics



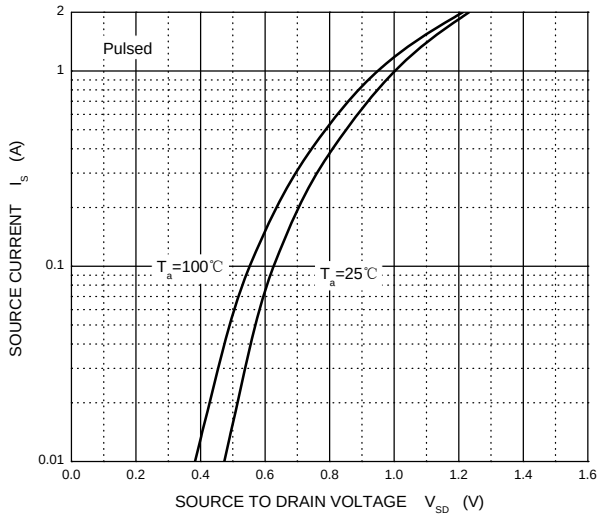
$R_{DS(ON)}$ ð ð I_D



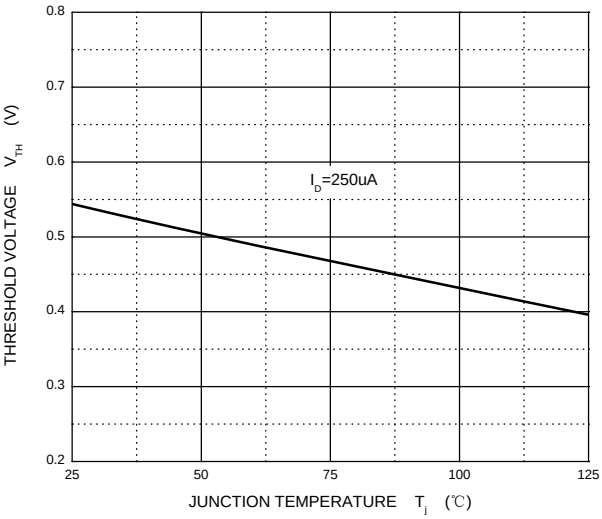
$R_{DS(ON)}$ ð ð V_{GS}



I_S ð ð V_{SD}



Threshold Voltage



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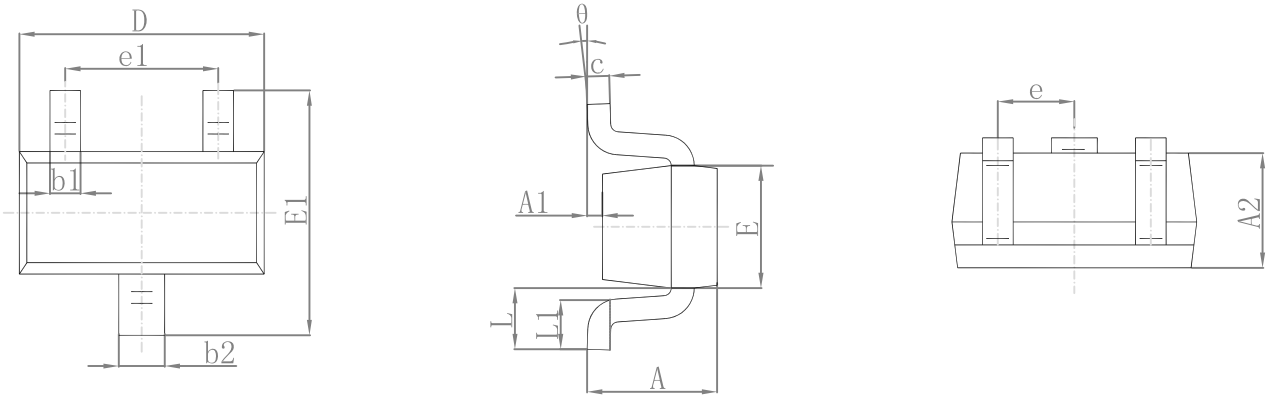
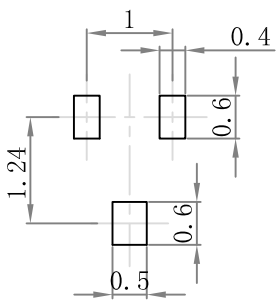
Package Outline Dimensions SOT-523



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.